Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

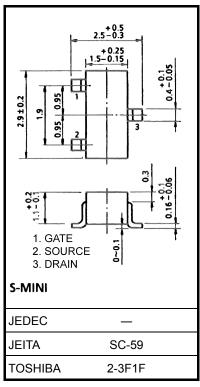
2SK1062

High Speed Switching Applications
Analog Switching Applications
Interface Applications

- Excellent switching time: $t_{on} = 14 \text{ ns (typ.)}$
- High forward transfer admittance: $|Y_{fs}| = 100 \text{ ms (min)}$ $@I_D = 50 \text{ mA}$
- Low on resistance: RDS (ON) = 0.6Ω (typ.) @ ID = 50 mA
- Enhancement-mode
- Complementary to 2SJ168

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC	I _D	200	mA	
	Pulse	I _{DP}	800		
Drain power dissipation (Ta = 25°C)		PD	200	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

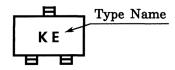


Weight: 0.012 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking



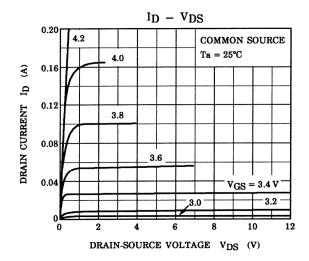


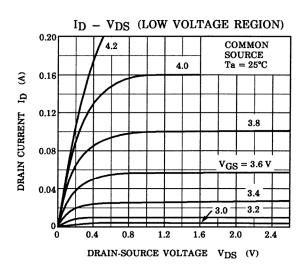
Electrical Characteristics (Ta = 25°C)

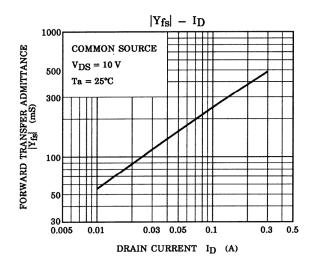
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curi	rent	I _{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$	_	_	±100	nA
Drain cut-off curre	ent	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0	_	_	10	μΑ
Drain-source brea	akdown voltage	V (BR) DSS	I _D = 1 mA, V _{GS} = 0	60	_	_	V
Gate threshold vo	ltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2	_	3.5	V
Forward transfer a	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 50 mA	100	_	_	mS
Drain-source ON	resistance	R _{DS} (ON)	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$		0.6	1.0	Ω
Drain-source ON	voltage	V _{DS} (ON)	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$		30	50	mV
Input capacitance		C _{iss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz		55	65	pF
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz		13	18	pF
Output capacitance		Coss	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz	_	40	50	pF
Switching time	Rise time	t _r	$I_{D} = 100 \text{ mA}$ $V_{IN} = 100 \text{ mA}$ $V_{DD} = 30 \text{ V}$ $V_{IN} : t_{r}, t_{f} < 5 \text{ ns}$ $D.U \le 1\% (Z_{out} = 50 \Omega)$	_	8	_	
	Turn-on time	t _{on}		_	14	_	ns
	Fall time	t _f			35		
	Turn-off Time	t _{off}			75		

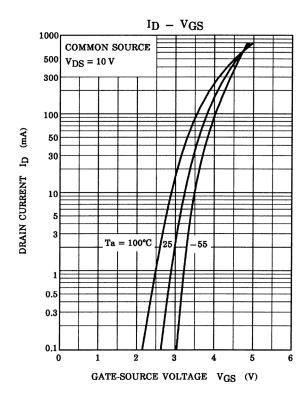
Note: This transistor is the electrostatic sensitive device. Please handle with caution.

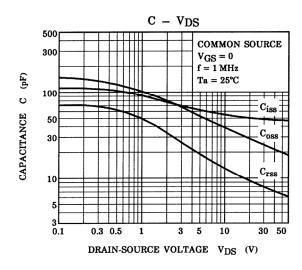
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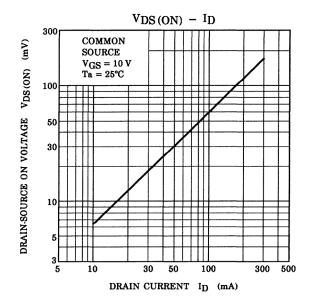


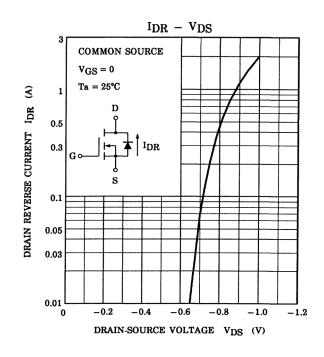


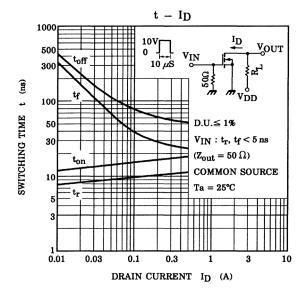


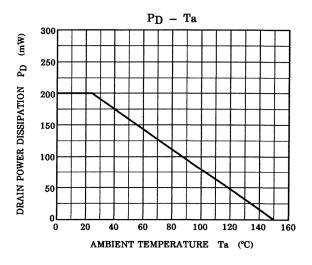












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20070701-EN GENERAL

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